

## **HIGH-SPEED** 16K X 16 DUAL-PORT STATIC RAM

IDT7026S/L

### **Features**

- True Dual-Ported memory cells which allow simultaneous access of the same memory location
- High-speed access
  - Military: 20/25/35/55ns (max.)
  - Industrial: 55ns (max.)
  - Commercial: 15/20/25/35/55ns (max.)
- Low-power operation
  - IDT7026S

Active: 750mW (typ.) Standby: 5mW (typ.)

- IDT7026L

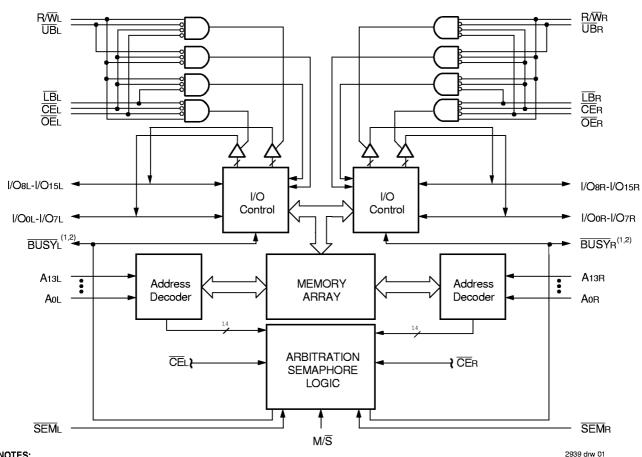
Active: 750mW (typ.) Standby: 1mW (typ.)

Separate upper-byte and lower-byte control for multi-

plexed bus compatibility

- IDT7026 easily expands data bus width to 32 bits or more using the Master/Slave select when cascading more than
- $M/\overline{S} = H$  for  $\overline{BUSY}$  output flag on Master,  $M/\overline{S} = L$  for  $\overline{BUSY}$  input on Slave
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- TTL-compatible, single 5V (±10%) power supply
- Available in 84-pin PGA and 84-pin PLCC
- Industrial temperature range (-40°C to +85°C) is available for selected speeds

## **Functional Block Diagram**



### NOTES:

- 1. (MASTER): BUSY is output; (SLAVE): BUSY is input.
- 2. BUSY outputs are non-tri-stated push-pull.

**JANUARY 1999** 

## **Description**

The IDT7026 is a high-speed 16K x 16 Dual-Port Static RAM. The IDT7026 is designed to be used as a stand-alone Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 32-bit-or-more word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 32-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

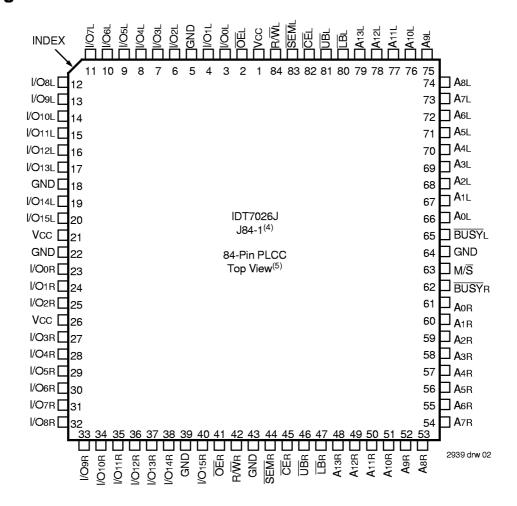
This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down

feature controlled by  $\overline{CE}$  permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CMOS high-performance technology, these devices typically operate on only 750mW of power.

The IDT7026 is packaged in a ceramic 84-pin PGA, and a 84-pin PLCC. Military grade product is manufactured in compliance with the latest revision of MIL-PRF-38535 QML, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

## Pin Configurations (1,2,3)



- 1. All Vcc pins must be connected to the power supply.
- 2. All GND pins must be connected to the ground supply.
- 3. Package body is approximately 1.15 in x 1.15 in x .17 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

## Pin Configurations(1,2,3) (con't.)

	63	61	60	58	55	54	51	48	46	45	42
11	I/O7L	I/O5L	I/O4L	I/O2L	I/Ool	ŌĒL	SEML	<u>LB</u> L	A12L	A11L	A <sub>8</sub> L
	66	64	62	59	56	49	50	47	44	43	40
10	I/O10L	I/O8L	I/O6L	I/O3L	I/O1L	ŪBL	CEL	A13L	A10L	A9L	A6L
	67	65			57	53	52			41	39
09	I/O11L	I/O9L		GND Vcc R/WL						A7L	<b>A</b> 5L
	69	68	1				•	•		38	37
08	I/O13L	I/O12L							<b>A</b> 4L	AзL	
	72	71	73						33	35	34
07	I/O15L	I/O14L	Vcc			IDT7026		BUSYL	A1L	Aol	
	75	70	74			G84-3 <sup>(4</sup>		32	31	36	
06	I/Oor	GND	GND	84-Pin PGA					GND	M/S	A <sub>2</sub> L
	76	77	78		Top Vliew <sup>(5)</sup>				28	29	30
05	I/O1R	I/O2R	Vcc						A1R	Aor	BUSYR
	79	80			26	27					
04	I/O3R	I/O4R								A3R	A2R
	81	83	1		7	11	12	]		23	25
03	I/O5R	I/O7R			GND	GND	SEMR			A6R	A4R
	82	1	2	5	8	10	14	17	20	22	24
02	I/O6R	I/O9R	I/O10R	I/O13R	I/O15R	R/WR	ŪBR	A12R	A9R	A7R	A5R
	84	3	4	6	9	15	13	16	18	19	21
01	I/O8R	I/O11R	I/O12R	I/O14R	ŌĒR	LBR	CER	A13R	A11R	A10R	A8R
1	Α	В	С	D	Е	F	G	Н	J	К	L
INDEX											2939 drw 0

### NOTES:

- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground supply.
- 3. Package body is approximately 1.12 in x 1.12 in x .16 in.
- 4. This package code is used to reference the package diagram.
- 5. This text does not indicate orientation of the actual part-marking.

### **Pin Names**

Left Port	Right Port	Names
CEL	CER	Chip Enable
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
A0L - A13L	A0R - A13R	Address
I/O0L - I/O15L	I/O0R - I/O15R	Data Input/Output
SEML	SEMR	Semaphore Enable
UBL	<del>UB</del> R	Upper Byte Select
LBL	<del>LB</del> R	Lower Byte Select
BUSYL	BUSYR	Busy Flag
N	/S	Master or Slave Select
V	cc	Power
G	ND	Ground

## **Maximum Operating Temperature** and Supply Voltage(1,2)

Grade	Ambient Temperature	GND	Vcc
Military	-55°C to+125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

2939 tbl 02

- 1. This is the parameter Ta.
- 2. Industrial temperature: for other speeds, packages and powers contact your

## Capacitance<sup>(1)</sup> (TA = +25°C, f = 1.0mhz)

Symbol	Param eter Param eter	Conditions <sup>(2)</sup>	Max.	Unit	
CIN	Input Capacitance	VIN = 3dV	9	pF	
Соит	Output Capacitance	Vout = 3dV	10	pF	

2939 tbl 03 NOTES:

- 1. This parameter is determined by device characterization but is not production
- 2. 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

## **Truth Table I - Non-Contention Read/Write Control**

		Inpu	ıts <sup>(1)</sup>			Out	puts	
CE	R/W	Œ	ŪB	ĪВ	SEM	I/O8-15	1/00-7	Mode
Н	Х	Х	Х	Х	Н	High-Z	High-Z	Deselected: Power-Down
Х	Х	Х	Н	Н	Н	High-Z	High-Z	Both Bytes Deselected
L	L	Х	L	Н	Н	DATAIN	High-Z	Write to Upper Byte Only
L	L	Х	Н	L	Н	High-Z	DATAIN	Write to Lower Byte Only
L	L	Х	L	L	Н	DATAIN	DATAIN	Write to Both Bytes
L	Н	L	L	Н	Н	DATAout	High-Z	Read Upper Byte Only
L	Н	L	Н	L	Н	High-Z	DATAout	Read Lower Byte Only
L	Н	٦	L	L	Н	DATAout	DATAout	Read Both Bytes
Х	Х	Н	Х	Х	Х	High-Z	High-Z	Outputs Disabled

NOTE:

1. AoL — A13L ≠ AoR — A13R.

2939 tbl 04

## Truth Table II - Semaphore Read/Write Control(1)

		Inp	outs			Outputs		
CE	R/W	Œ	<u>IB</u>	<u>IВ</u>	SEM	I/O8-15	1/00-7	Mode
Н	Н	L	Х	Х	L	DATAout	DATAout	Read Data in Semaphore Flag
Х	Н	L	Н	Н	L	DATAout	DATAout	Read Data in Semaphore Flag
Н	<b>↑</b>	Х	Х	Х	L	DATAIN	DATAIN	Write I/O <sub>0</sub> into Semaphore Flag
Х	<b>↑</b>	Х	Н	Н	L	DATAIN	DATAIN	Write I/O <sub>0</sub> into Semaphore Flag
L	Х	Х	L	Х	L			Not Allowed
L	Х	Х	Х	L	L			Not Allowed

NOTE: 2939 tol 05

## **Absolute Maximum Ratings**(1)

Symbol	Rating	Commercial & Industrial	Military	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	٧
TBIAS	Temperature Under Bias	-55 to +125	-65 to +135	°C
Tstg	Storage Temperature	-55 to +125	-65 to +150	°C
lout	DC Output Current	50	50	mA

NOTES:

<sup>1.</sup> There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O1s). These eight semaphores are addressed by Ao - A2.

<sup>1.</sup> Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

<sup>2.</sup> VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ Vcc + 10%.

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# **Recommended DC Operating Conditions**

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	٧
GND	Ground	0	0	0	٧
ViH	Input High Voltage	2.2	_	6.0(2)	٧
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>	_	0.8	٧

NOTES:

- 1.  $V \Vdash \ge -1.5V$  for pulse width less than 10ns.
- 2. VTERM must not exceed Vcc + 10%.

# DC Electrical Characteristics Over the Operating Temperature and Supply Soltage Range (Vcc = 5.0V ± 10%)

			7026S		70:		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
[Iu]	Input Leakage Current <sup>(1)</sup>	Vcc = 5.5V, Vin = 0V to Vcc	_	10	_	5	μΑ
[ILO]	Output Leakage Current	CE = VIH, Vout = 0V to Vcc	_	10	_	5	μA
Vol	Output Low Voltage	IoL = 4mA	_	0.4	_	0.4	٧
Vон	Output High Voltage	loн = -4mA	2.4	-	2.4	_	٧

2939 tbl 07

NOTE:

1. At Vcc = 2.0V, input leakages are undefined.

### **AC Test Conditions**

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	Figures 1 and 2

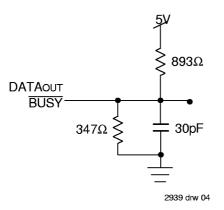


Figure 1. AC Output Test Load

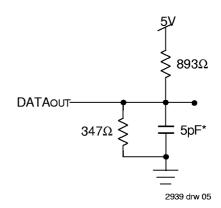


Figure 2. Output Test Load (for tlz, tHz, twz, tow) \* Including scope and jig.

# DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(1,5)</sup> (con't.) (Vcc = 5.0V ± 10%)

					7026 Com'l		7026X20 Com'l & Military.		7026X25 Com'l & Military		
Symbol	Parameter	Test Condition	Versi	Version		Max.	Тур.(2)	Max.	Тур.(2)	Max.	Un
Icc	Dynamic Operating Current (Both Ports Active)	CE = VIL, Outputs Open SEM = VIH	COM'L	S L	190 190	325 285	180 180	315 275	170 170	305 265	m
		f = fMAX <sup>(3)</sup>	MIL & S — — — IND L — —	180 180	355 315	170 170	345 305				
	Standby Current (Both Ports - TTL Level	CEL = CER = VH SEMR = SEML = VH f = fMAX <sup>(3)</sup>	COM'L	S L	35 35	95 70	30 30	85 60	25 25	85 60	r
	inpus)	T = TMAX <sup>(c)</sup>	MIL & IND		_	_	30 30	100 80	25 25	100 80	
ISB2	Standby Current (One Port - TTL Level Inputs)	CE"A" = VIL and CE"B" = VIH <sup>(5)</sup> Active Port Outputs Open,	COM'L		115 115	210 180	105 105	200 170	r		
		SEMR = SEML = VIH	MIL & IND	S L	_		115 115	245 210	105 105	80 5 200 170 6 230 5 200	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports CEL and CER ≥ VCC - 0.2V VN ≥ VCC - 0.2V or	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	1.0 0.2	15 5	ľ
	inpus)	VN ≤ 0.2V, f = 0 <sup>(4)</sup> SEMR = SEML ≥ VCC - 0.2V	MIL & IND	S L		1 1	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level	CE"A" ≤ 0.2V and CE"B" ≥ Vcc - 0.2V <sup>(5)</sup> SEMR = SEML ≥ Vcc - 0.2V	COM'L	S L	120 120	195 170	110 110	185 160	100 100	170 145	r
Inputs)	SEIVIR = SEIVIL $\geq$ VCC - 0.2V VN $\geq$ VCC - 0.2V or VIN $\leq$ 0.2V Active Port Outputs Open, $f=f_{MA}x^{(3)}$	MIL & IND	S L	_	-	110 110	210 185	100 100	200 175		

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		Parameter Test Condition			7026 Com Mili	'l &	7026X55 Com'l, Ind & Military		
Symbol	Parameter			on	Typ. <sup>(2)</sup>	Max.	Typ. <sup>(2)</sup>	Max.	Unit
Icc	Dynamic Operating Current (Both Ports Active)	CE = VIL, Outputs Open SEM = VIH f = flwa x <sup>(3)</sup>		S L	160 160	295 255	150 150	270 230	mA
	, ,	T = IMAX**	MIL & IND	S L	160 160	335 295	150 150	310 270	
ISB1	(Both Ports - TTL Level	CEL = CER = VIH SEMR = SEML = VIH f = fMAX <sup>(3)</sup>	COM'L	S L	20 20	85 60	13 13	85 60	mA
		T = IMAX*	MIL & IND	S L	20 20	100 80	13 13	100 80	
ISB2	Standby Current (One Port - TTL Level Inputs)	CE"A" = VIL and CE"B" = VIH <sup>(5)</sup> Active Port Outputs Open, f=ftMaX <sup>(3)</sup>	COM'L	S L	95 95	185 155	85 85	165 135	mA
	mpus)	SEMR = SEML = VH	MIL & IND	S L	95 95	215 185	85 85	195 165	
ISB3	Full Standby Current (Both Ports - All CMOS Level Inputs)	Both Ports CEL and CER ≥ VCC - 0.2V	COM'L	S L	1.0 0.2	15 5	1.0 0.2	15 5	mA
	Level lipus)		MIL & IND	S L	1.0 0.2	30 10	1.0 0.2	30 10	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	CE"A" ≤ 0.2V and CE"B" ≥ VCC - 0.2V <sup>(5)</sup> SEMR = SEML ≥ VCC - 0.2V	COM'L	S L	90 90	160 135	80 80	135 110	mA
	Level inpute)	SEIVIR - SEIVIL 2 VCC - V.2V Vn ≥ VCC - 0.2V or Vn ≤ 0.2V Active Port Outputs Open FfMaX <sup>(3)</sup>	MIL & IND	S L	90 90	190 165	80 80	175 150	

- 1. 'X' in part numbers indicates power rating (S or L).
- Vcc = 5V, Ta = +25°C, and are not production tested. Iccpc = 120mA (Typ.)
   At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tac, and using "AC Test Conditions" of input levels of GND to 3V.
   f = 0 means no address or control lines change.
- 5. Industrial temperature: for other speeds, packages and powers contact your sales office.

## **AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range** (4,5)

			6X15 I Only	Con	6X20 n'I & itary		6X25 Military	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
READ CYCLE								
trc	Read Cycle Time	15	_	20	_	25	_	ns
taa	Address Access Time	_	15	_	20	_	25	ns
tace	Chip Enable Access Time <sup>(3)</sup>	_	15	_	20	_	25	ns
tabe	Byte Enable Access Time <sup>(3)</sup>	_	15	_	20	_	25	ns
taoe	Output Enable Access Time	_	10	_	12	_	13	ns
toн	Output Hold from Address Change	3	_	3	_	3	_	ns
t.z	Output Low-Z Time <sup>(1,2)</sup>	3	_	3	_	3	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10	_	12	_	15	ns
<b>t</b> PU	Chip Enable to Power Up Time <sup>(2)</sup>	0	_	0	_	0	_	ns
tPD tPD	Chip Disable to Power Down Time <sup>(2)</sup>	_	15	_	20	_	25	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10	_	10		12	_	ns
tsaa	Semaphore Address Access Time	_	15	_	20	_	25	ns

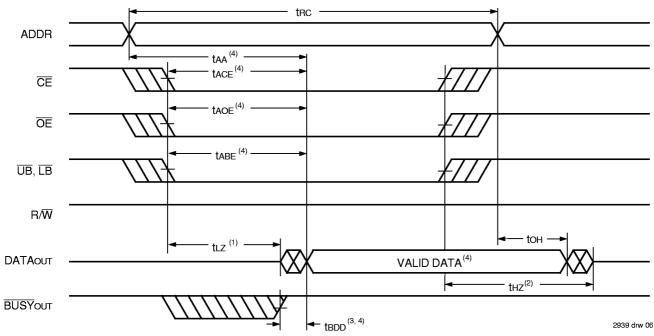
2939 tbl 12a

		Con	SX35 n'I & tary	702 Com' & Mi		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE						
trc	Read Cycle Time	35	_	55	_	ns
taa	Address Access Time	_	35	_	55	ns
tace	Chip Enable Access Time <sup>(3)</sup>	_	35	_	55	ns
tabe	Byte Enable Access Time <sup>(3)</sup>	_	35	_	55	ns
taoe	Output Enable Access Time	_	20	_	30	ns
toн	Output Hold from Address Change	3	_	3	_	ns
tı.z	Output Low-Z Time <sup>(1,2)</sup>	3	_	3	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	15	_	25	ns
t₽U	Chip Enable to Power Up Time <sup>(2)</sup>	0	_	0	_	ns
tPD	Chip Disable to Power Down Time <sup>(2)</sup>	_	35	_	50	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	15	_	15	_	ns
tsaa	Semaphore Address Access Time	_	35	_	55	ns

2939 tbl 12b

- Transition is measured ±200mV from Low or High-impedance voltage with Output Test Load (Figure 2).
   This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access RAM,  $\overline{CE}$  = VIL and  $\overline{SEM}$  = VIH. To access semaphore,  $\overline{CE}$  = VIH and  $\overline{SEM}$  = VIL.
- 4. 'X' in part numbers indicates power rating (S or L).
- 5. Industrial temperature: for other speeds, packages and powers contact your sales office.

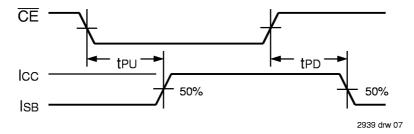
## **WAVEFORM OF READ CYCLES**(5)



#### NOTES:

- 1. Timing depends on which signal is asserted last,  $\overline{OE}$ ,  $\overline{CE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
- 2. Timing depends on which signal is de-asserted first  $\overline{CE}$ ,  $\overline{OE}$ ,  $\overline{LB}$ , or  $\overline{UB}$ .
- 3. tbdd delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5.  $\overline{\text{SEM}} = \text{V}_{\text{IH}}$ .

## **Timing of Power-Up Power-Down**



## AC Electrical Characteristics Over the Operating Temperature and Supply Voltage<sup>(5,6)</sup>

Symbol	Parameter		6X15 I Only	7026X20 Com'l & Military		7026X25 Com'l & Military		
•		Min.	Max.	Min.	Max.	Min.	Max.	Unit
WRITE CYCL	E							-
twc	Write Cycle Time	15	_	20	_	25	_	ns
tew	Chip Enable to End-of-Write <sup>(3)</sup>	12	_	15	_	20	_	ns
taw	Address Valid to End-of-Write	12	_	15	_	20	_	ns
tas	Address Set-up Time <sup>(3)</sup>	0	_	0	_	0	_	ns
twp	Write Pulse Width	12	_	15	_	20	_	ns
twr	Write Recovery Time	0	_	0	_	0	_	ns
tow	Data Valid to End-of-Write	10	_	15	_	15	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	10	_	12	_	15	ns
tDH	Data Hold Time <sup>(4)</sup>	0	_	0	_	0	_	ns
twz	Write Enable to Output in High-Z <sup>(1,2)</sup>	_	10	_	12	_	15	ns
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0	_	0	_	0	_	ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	5	_	ns
tsps	SEM Flag Contention Window	5	_	5	_	5	_	ns

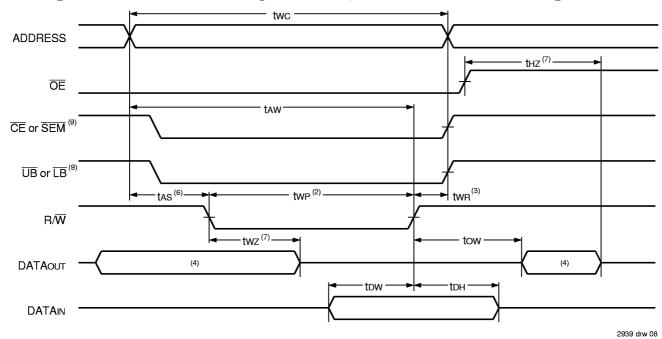
3199 tbl 13a

2939 tbl 13b

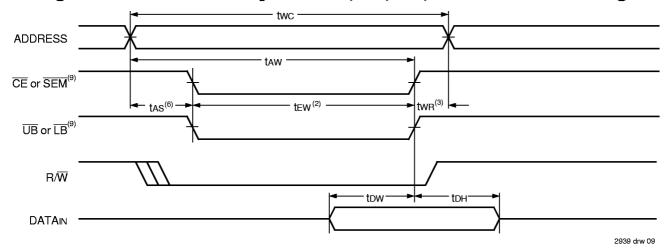
Symbol	Parameter	Con	6X35 n'I & itary	7020 Com & Mi		
		Min.	Max.	Min.	Max.	Unit
WRITE CYCLI	E					
twc	Write Cycle Time	35	_	55	_	ns
tew	Chip Enable to End-of-Write <sup>(3)</sup>	30	_	45	_	ns
taw	Address Valid to End-of-Write	30	_	45	_	ns
tas	Address Set-up Time <sup>(3)</sup>	0	_	0	_	ns
twp	Write Pulse Width	25	_	40	_	ns
twr	Write Recovery Time	0	_	0	_	ns
tow	Data Valid to End-of-Write	15	_	30	_	ns
tHZ	Output High-Z Time <sup>(1,2)</sup>	_	15	_	25	ns
toн	Data Hold Time <sup>(4)</sup>	0	_	0	_	ns
twz	Write Enable to Output in High-Z <sup>1,2)</sup>	_	15	_	25	ns
tow	Output Active from End-of-Write <sup>(1,2,4)</sup>	0	_	0	_	ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	ns
tsps	SEM Flag Contention Window	5	_	5	_	ns

- 1. Transition is measured ±200mV from Low or High-impedance voltage with Output Test Load (Figure 2).
- 2. This parameter is guaranteed by device characterization, but is not production tested.
- 3. To access RAM,  $\overrightarrow{CE} = V_{IL}$  and  $\overrightarrow{SEM} = V_{IH}$ . To access semaphore,  $\overrightarrow{CE} = V_{IH}$  and  $\overline{SEM} = V_{IL}$ . Either condition must be valid for the entire tew time.
- 4. The specification for toh must be met by the device supplying write data to the RAM under all operating conditions. Although toh and tow values will vary over voltage and temperature, the actual toh will always be smaller than the actual tow.
- 5. 'X' in part numbers indicates power rating (S or L).
- 6. Industrial temperature: for other speeds, packages and powers contact your sales office.

## Timing Waveform of Write Cycle No. 1, R/W Controlled Timing(1,5,8)

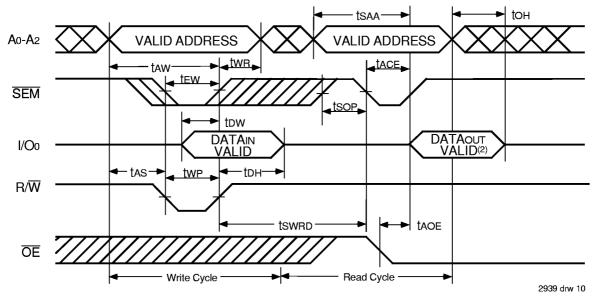


## Timing Waveform of Write Cycle No. 2, $\overline{\text{CE}}$ , $\overline{\text{UB}}$ , $\overline{\text{LB}}$ Controlled Timing<sup>(1,5)</sup>



- 1.  $R/\overline{W}$  or  $\overline{CE}$  or  $\overline{UB}$  and  $\overline{LB}$  = VIH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a VIL  $\overline{\text{CE}} = \text{VIL}$  and  $\overline{\text{R/W}} = \text{VIL}$  for memory array writing cycle.
- 3. twn is measured from the earlier of  $\overline{CE}$  or  $\overline{R/W}$  (or  $\overline{SEM}$  or  $\overline{R/W}$ ) going ViH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the  $\overline{\text{CE}}$  or  $\overline{\text{SEM}} = \text{VIL}$  transition occurs simultaneously with or after the  $\overline{\text{RW}} = \text{VIL}$  transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last,  $\overline{\text{CE}}$  or  $\overline{\text{R/W}}$ .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured ±200mV from steady state with the Output Test Load (Figure 2).
- 8. If  $\overline{OE} = V_{IL}$  during  $R\overline{W}$  controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If  $\overline{OE} = V_{IH}$  during an  $R\overline{W}$  controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM,  $\overline{\text{CE}} = \text{VIL}$  and  $\overline{\text{SEM}} = \text{VIH}$ . To access semaphore,  $\overline{\text{CE}} = \text{VIH}$  and  $\overline{\text{SEM}} = \text{VIL}$ . tew must be met for either condition.

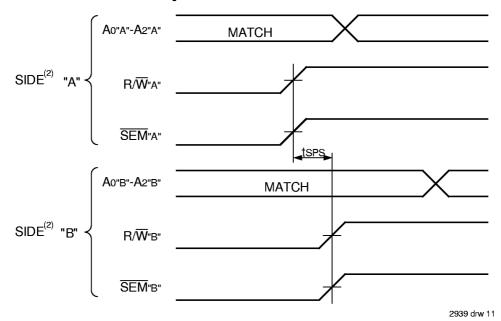
## Timing Waveform of Semaphore Read after Write Timing, Either Side(1)



#### NOTES

- 1.  $\overline{CE} = VIH \text{ or } \overline{UB} \text{ and } \overline{LB} = VIH \text{ for the duration of the above timing (both write and read cycle).}$
- 2. "DATAOUT VALID" represents all I/O's (I/Oo-I/O15) equal to the semaphore value.

## Timing Waveform of Semaphore Write Contention (1,3,4)



- 1. Dor = Dol = VIL,  $\overline{CER} = \overline{CEL} = VIH$ , or both  $\overline{UB} \& \overline{LB} = VIH$ .
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. Port "B" is the opposite from port "A".
- 3. This parameter is measured from R/W'A' or SEM'A' going HIGH to R/W'B' or SEM'B' going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

# AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range<sup>(6,7)</sup>

			6X15 I Only	Con	6X20 n'I & itary	Con	6X25 n'l & itary	
Symbol	Parameter	Min.	Max.	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	(M/S=ViH)							
<b>t</b> BAA	BUSY Access Time from Address Match	_	15	_	20	_	20	ns
<b>t</b> BDA	BUSY Disable Time from Address Not Matched	_	15	_	20	_	20	ns
<b>t</b> BAC	BUSY Access Time from Chip Enable Low	_	15	_	20	_	20	ns
tBDC	BUSY Access Time from Chip Enable High	_	15	_	17	_	17	ns
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5	_	5	_	5	_	ns
tBDD	BUSY Disable to Valid Data	_	18	_	30	_	30	ns
twн	Write Hold After BUSY <sup>(5)</sup>	12	_	15	_	17	_	ns
BUSY TIMING	(M/S=VIL)							
twB	BUSY Input to Write <sup>(4)</sup>	0	_	0	_	0	_	ns
twн	Write Hold After BUSY <sup>(5)</sup>	12	_	15	_	17	_	ns
PORT-TO-POR	T DELAY TIMING							
twoo	Write Pulse to Data Delay <sup>(1)</sup>	_	30	_	45	_	50	ns
topo	Write Data Valid to Read Data Delay(1)	_	25	_	30	_	35	ns

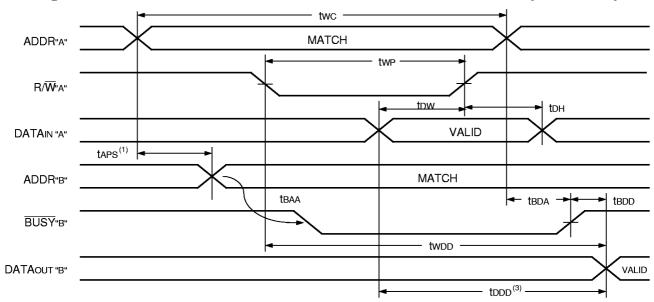
2939 tbl 14a

			6X35 Military	Com	6X55 'I, Ind litary		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit	
BUSY TIMING	(M/S=Vih)						
<b>t</b> BAA	BUSY Access Time from Address Match	_	20	_	45	ns	
<b>t</b> BDA	BUSY Disable Time from Address Not Matched	_	20	_	40	ns	
<b>t</b> BAC	BUSY Access Time from Chip Enable Low	_	20	_	40	ns	
tBDC	BUSY Access Time from Chip Enable High	_	20	_	35	ns	
taps	Arbitration Priority Set-up Time <sup>(2)</sup>	5	_	5	_	ns	
tBDD	BUSY Disable to Valid Data <sup>(3)</sup>	_	35	_	40	ns	
twн	Write Hold After BUSY <sup>(5)</sup>	25	_	25	_	ns	
BUSY TIMING	(M/S=VIL)						
twB	BUSY Input to Write <sup>(4)</sup>	0	_	0	_	ns	
twн	Write Hold After BUSY <sup>(5)</sup>	25	_	25	_	ns	
PORT-TO-POR	T DELAY TIMING						
twoo	Write Pulse to Data Delay <sup>(1)</sup>	_	60	_	80	ns	
tooo	Write Data Valid to Read Data Delay <sup>(1)</sup>	_	45	_	65	ns	

2939 tbl 14b

- 1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VIH)".
- 2. To ensure that the earlier of the two ports wins.
- 3. tBDD is a calculated parameter and is the greater of 0, twDD twP (actual), or tDDD tDW (actual).
- 4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".
- 5. To ensure that a write cycle is completed on port "B" after contention on port "A".
- 6. 'X' in part numbers indicates power rating (S or L).
- 7. Industrial temperature: for other speeds, packages and powers contact your sales office.

## Timing Waveform of Write with Port-to-Port Read and $\overline{BUSY}$ (M/ $\overline{S}$ = VIH)(2,4,5)

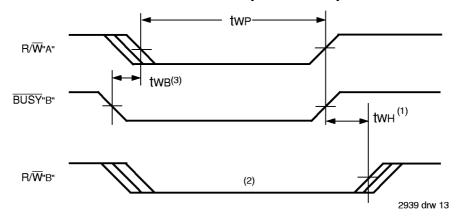


### NOTES:

2939 drw 12

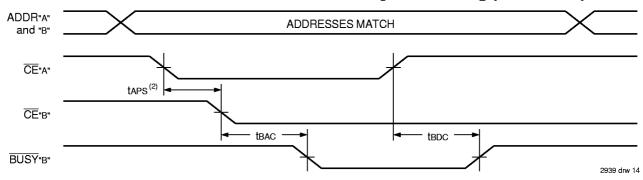
- 1. To ensure that the earlier of the two ports wins. taps is ignored for  $M/\overline{S} = V \perp (slave)$ .
- 2.  $\overline{CE}L = \overline{CE}R = VIL$ .
- 3.  $\overline{OE} = V_{IL}$  for the reading port.
- 4. If  $M/\overline{S} = VIL$  (slave),  $\overline{BUSY}$  is an input. Then for this example  $\overline{BUSY}A' = VIH$  and  $\overline{BUSY}B'$  input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

## Timing Waveform of Write with $\overline{BUSY}$ (M/ $\overline{S}$ = VIL)

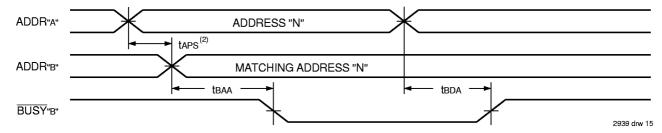


- 1. twn must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twB is only for the "SLAVE" version.

## Waveform of $\overline{BUSY}$ Arbitration Controlled by $\overline{CE}$ Timing (M/ $\overline{S}$ = ViH)(1)



# Waveform of $\overline{BUSY}$ Arbitration Cycle Controlled by Address Match Timing (M/ $\overline{S}$ = ViH)<sup>(1)</sup>



### NOTES:

- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from "A".
- 2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

## Truth Table III — Example of Semaphore Procurement Sequence(1,2,3)

	•	-	<b>-</b>
Functions	Do - D15 Left	Do - D15 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

### NOTES:

- 1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7026.
- 2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O16). These eight semaphores are addressed by Ao A2.
- 3.  $\overline{\text{CE}} = \text{VIH}, \ \overline{\text{SEM}} = \text{VIL}$  to access the semaphores. Refer to the semaphore Read/Write Control Truth Table.

## Truth Table IV — Address BUSY Arbitration

	In	puts	Out	puts	
CEL	CER	Aol-A13L Aor-A13R	BUSY <sub>L</sub> (1)	BUSYR <sup>(1)</sup>	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit <sup>(3)</sup>

NOTES: 2939 (D) 16

- Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSYx outputs on the IDT7026 are push pull, not open drain outputs. On slaves the BUSYx input internally inhibits writes.
- LOW if the inputs to the opposite port were stable prior to the address and enable
  inputs of this port. HIGH if the inputs to the opposite port became stable after the
  address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR
  = LOW will result. BUSYL and BUSYR outputs cannot be LOW simultaneously.
- Writes to the left port are internally ignored when BUSYL outputs are driving LOW
  regardless of actual logic level on the pin. Writes to the right port are internally
  ignored when BUSYR outputs are driving LOW regardless of actual logic level
  on the pin.

## **Functional Description**

The IDT7026 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7026 has an automatic power down feature controlled by  $\overline{\text{CE}}$ . The  $\overline{\text{CE}}$  controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ( $\overline{\text{CE}}$  = VIH). When a port is enabled, access to the entire memory array is permitted.

## **Busy Logic**

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The  $\overline{\text{BUSY}}$  pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a  $\overline{\text{BUSY}}$  indication, the write signal is gated internally to prevent the write from proceeding.

The use of  $\overline{BUSY}$  logic is not required or desirable for all applications. In some cases it may be useful to logically OR the  $\overline{BUSY}$  outputs together and use any  $\overline{BUSY}$  indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of  $\overline{BUSY}$  logic is not desirable, the  $\overline{BUSY}$  logic can be disabled by placing the part in slave mode with the M/ $\overline{S}$  pin. Once in slave mode the  $\overline{BUSY}$  pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the  $\overline{BUSY}$  pins HIGH. If desired, unintended write operations can be prevented to a port by tying the  $\overline{BUSY}$  pin for that port LOW.

The BUSY outputs on the IDT 7026 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

## Width Expansion with BUSY Logic Master/Slave Arrays

When expanding an IDT7026 RAM array in width while using  $\overline{BUSY}$  logic, one master part is used to decide which side of the RAM array will receive a  $\overline{BUSY}$  indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the  $\overline{BUSY}$  signal as a write inhibit signal. Thus on the IDT7026 RAM the  $\overline{BUSY}$  pin is an output if the part is used as a master (M/ $\overline{S}$  pin = VIH), and the BUSY pin is an input if the part used as a slave (M/ $\overline{S}$  pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the

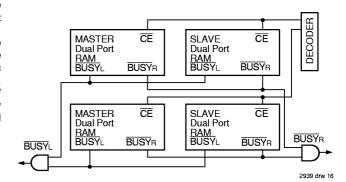


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7026 RAMs.

array and another master indicating  $\overline{BUSY}$  on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The  $\overline{BUSY}$  arbitration on a master is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a  $\overline{BUSY}$  flag to be output from the master before the actual write pulse can be initiated with either the  $R/\overline{W}$  signal or the byte enables. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

## **Semaphores**

The IDT7026 is an extremely fast Dual-Port  $16K \times 16$  CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical infunction to standard CMOS Static RAM and can be read from, or written to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts

in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by  $\overline{CE}$ , the Dual-Port RAM enable, and  $\overline{SEM}$ , the semaphore enable. The  $\overline{CE}$  and  $\overline{SEM}$  pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table I where  $\overline{CE}$  and  $\overline{SEM} = VIH$ .

Systems which can best use the IDT7026 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7026's hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7026 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

## **How the Semaphore Flags Work**

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT7026 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a LOW input on the  $\overline{\text{SEM}}$  pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address,  $\overline{\text{OE}}$ , and  $R/\overline{W}$ ) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins Ao-A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table III). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a

one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select ( $\overline{SEM}$ ) and output enable ( $\overline{OE}$ ) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal ( $\overline{SEM}$  or  $\overline{OE}$ ) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table III). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that

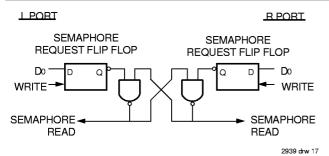


Figure 4. IDT7026 Semaphore Logic

semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

## **Using Semaphores—Some Examples**

Perhaps the simplest application of semaphores is their application as resource markers for the IDT7026's Dual-Port RAM. Say the 16K  $\times$  16 RAM was to be divided into two 8K  $\times$  16 blocks which were to be dedicated at any one time to servicing either the left or right port. Semaphore 0 could be used to indicate the side which would control the lower section of memory, and Semaphore 1 could be defined as the indicator for the upper section of memory.

To take a resource, in this example the lower 8K of Dual-Port RAM, the processor on the left port could write and then read a zero in to Semaphore 0. If this task were successfully completed (a zero was read back rather than a one), the left processor would assume control of the lower 8K. Meanwhile the right processor was attempting to gain control of the resource after the left processor, it would read back a one in response to the zero it had attempted to write into Semaphore 0. At this point, the software could choose to try and gain control of the second 8K

section by writing, then reading a zero into Semaphore 1. If it succeeded in gaining control, it would lock out the left side.

Once the left side was finished with its task, it would write a one to Semaphore 0 and may then try to gain access to Semaphore 1. If Semaphore 1 was still occupied by the right side, the left side could undo its semaphore request and perform other tasks until it was able to write, then read a zero into Semaphore 1. If the right processor performs a similar task with Semaphore 0, this protocol would allow the two processors to swap 8K blocks of Dual-Port RAM with each other.

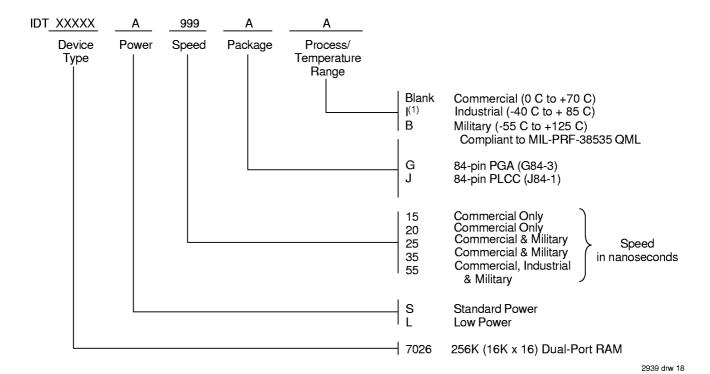
The blocks do not have to be any particular size and can even be variable, depending upon the complexity of the software using the semaphore flags. All eight semaphores could be used to divide the Dual-Port RAM or other shared resources into eight parts. Semaphores can even be assigned different meanings on different sides rather than being given a common meaning as was shown in the example above.

Semaphores are a useful form of arbitration in systems like disk interfaces where the CPU must be locked out of a section of memory during a transfer and the I/O device cannot tolerate any wait states. With the use of semaphores, once the two devices has determined which memory area was "off-limits" to the CPU, both the CPU and the I/O devices could access their assigned portions of memory continuously without any wait states.

Semaphores are also useful in applications where no memory "WAIT" state is available on one or both sides. Once a semaphore handshake has been performed, both processors can access their assigned RAM segments at full speed.

Another application is in the area of complex data structures. In this case, block arbitration is very important. For this application one processor may be responsible for building and updating a data structure. The other processor then reads and interprets that data structure. If the interpreting processor reads an incomplete data structure, a major error condition may exist. Therefore, some sort of arbitration must be used between the two different processors. The building processor arbitrates for the block, locks it and then is able to go in and update the data structure. When the update is completed, the data structure block is released. This allows the interpreting processor to come back and read the complete data structure, thereby guaranteeing a consistent data structure.

## **Ordering Information**



### NOTE:

Industrial temperature range is available on selected PLCC packages in standard power.
 For other speed, packages and powers contact your sales office.

## **Datasheet Document History**

1/14/99: Initiated datasheet document history

Converted to new format

Cosmetic and typographical corrections

Pages 2 and 3 Added additional notes to pin configurations



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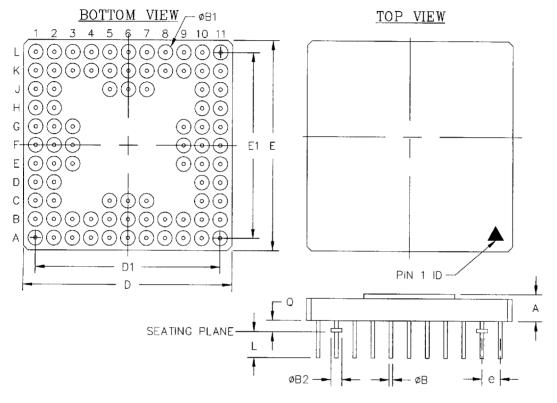
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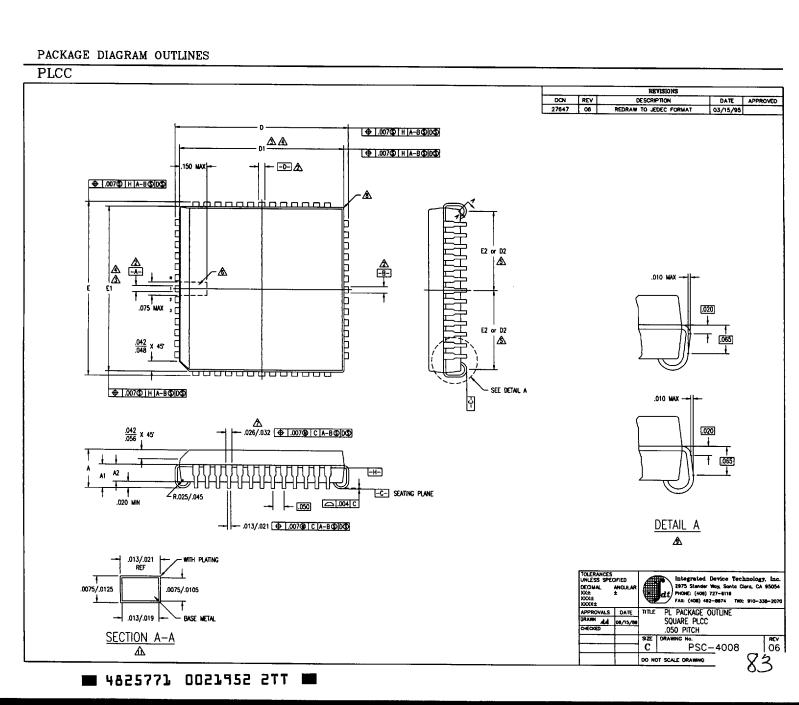
### PIN GRID ARRAYS (Continued)

### 84 PIN PGA (CAVITY UP - 11 X 11 GRID)



DWG #	G84	1-3			
# OF PINS (N)	84				
SYMBOL	MIN	MAX			
Α	.070	.145			
ØΒ	.016	.020			
øB1	_	.080			
øB2	.040	.060			
D/E	1.080	1.120			
D1/E1	1.000	BSC			
е	.100	BSC			
L	.120	.140			
М	1	1			
Q	.040	.060			

- 1. ALL DIMENSIONS ARE IN INCHES, UNLESS OTHERWISE SPECIFIED.
- 2. BSC BASIC LEAD SPACING BETWEEN CENTERS.
- 3. SYMBOL "M" REPRESENTS THE PGA MATRIX SIZE.4. SYMBOL "N" REPRESENTS THE NUMBER OF PINS
- 5. CHAMFERED CORNERS ARE IDT'S OPTION.



## PACKAGE DIAGRAM OUTLINES

## PLCC (Continued)

		REVISIONS		
DCN	REV	DESCRIPTION	DATE	APPROVED
27647	06	REDRAW TO JEDEC FORMAT	03/15/95	

	DWG #		J28-	1	DWG	1	J44-	1	DWG	1	J52-	1	DWG	#	J68-	1	DWG	#	J84-	1
Ş	JEDE	C VARIAT	ION	N	JEDE	C VARIAT	ION	N	JEDE	C VARIAT	ion .	N	JEDE	C VARIAT	10N	N	JEDE	C VARIAT	ION	
9		AB		] 🖁		AC		] P		AD		🖁		AE		P		AF		ļĝ
Ľ	MIN	NOM	MAX	E	MIN	NOM	MAX	É	MIN	NOM	MAX	Ė	MIN	NOM	MAX	È	MIN	NOM	MAX	Ė
A	.165	.172	.180		.165	.172	.180		.165	.172	.180		.165	.172	.180		.165	.172	.180	
A1	.095	.105	.115		.095	.105	.115		.095	.105	.115		.095	.105	.115		.095	.105	.115	_
A2	.062	_	.083		.062	-	.083		.062	T -	.083		.062	-	.083	М	.059	-	.080	_
D	.485	.490	.495		.685	.690	.695		.785	.790	.795		.985	.990	.995		1.185	1,190	1.195	
D1	.450	.453	.456	3,4	.650	.653	.656	3,4	.750	.753	.756	3,4	.950	.953	.956	3.4	1,150	1.154	1,156	3.4
D2	.195	.205	.215	5	.295	.305	.315	5	.345	.355	.365	5	.445	.455	.465	5	.545	.555	.565	5
Ε	.485	.490	.495		.685	.690	.695		.785	.790	.795		.985	.990	.995		1.185	1,190	1,195	- <u>-</u>
E١	.450	.453	.456	3,4	.650	.653	656	3,4	.750	.753	.756	3,4	.950	953	.956	3,4	1,150	1.154	1.156	3,4
E2	.191	.205	.219	5	.291	.305	.319	5	.341	.355	.369	5	.441	.455	.469	5	.541	.555	.569	5
N		28				44			1	52				68				84		Ť

### NOTES:

1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982

DATUMS A-B AND -D- TO BE DETERMINED AT DATUM PLANE -H-

⚠ DIMENSIONS D1 AND E1 ARE TO BE DETERMINED AT DATUM PLANE —H—

⚠ DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE MOLD PROTRUSION IS .010 PER SIDE. D1 AND E1 ARE BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH

△ DIMENSIONS D2 AND E2 ARE TO BE DETERMINED AT SEATING PLANE —C—CONTACT POINT

DETAIL OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED

LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .007 TOTAL MAXIMUM PER LEAD

**A** EXACT SHAPE OF EACH CORNER IS OPTIONAL

10 ALL DIMENSIONS ARE IN INCHES

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THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MS-018, VARIATION AB, AC, AD, AE & AF. EXCEPTIONS: JEDEC MAXIMUM BASE METAL LEAD WIDTH IS .018

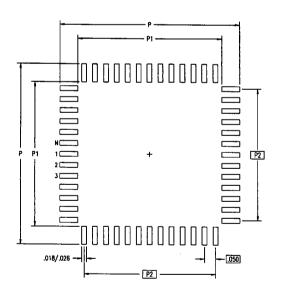
TOLERANCES UNLESS SPEI DECIMAL XX± XXX± XXXX±			Integrated Device Technology, Inc. 2975 Stender Way, Santa Clare, CA 95054 PHONE: (408) 727-8116 FAX: (408) 492-8674 TWX: 910-338-2070							
APPROVALS	DATE	TITLE	PL PACKAGE OUTLI	NE						
DRAWN ALA	08/15/86	1	SQUARE PLCC							
CHECKED		1	.050 PITCH							
		SIZE	DRAWING No.		REV					
		С	PSC-40	800	06					
		DO NO	T SCALE DRAWING	01	1					
				0,	٦					

### PACKAGE DIAGRAM OUTLINES

## PLCC (Continued)

1	REVISIONS							
	DCN	Æ	DESCRIPTION	DATE	APPROVED			
	27647	8	REDRAW TO JEDEC FORMAT	03/15/95				

## LAND PATTERN DIMENSIONS



	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
P	.520	.528	.720	.728	.820	.828	1.020	1.028	1.220	1.228
P1	.354	.362	.554	.562	.654	.662	.854	.862	1.054	1.062
P2	.300 BSC		.500	.500 BSC .600		D BSC .800		0 BSC   1.00		BSC
N	28			14	52		68		84	

TOLERANCES UNLESS SPE DECIMAL XX± XXX± XXXX± XXXX±			Integrated Device Technolog 2975 Stender Woy, Sonto Clora, CA PHONE: (408) 727-8116 FAX: (408) 482-8674 TWX: 910-3	95054
APPROVALS	DATE	TITLE	PL PACKAGE OUTLINE	
DRAWN ALL	08/15/89		SQUARE PLCC	
CHECKED		ŀ	.050 PITCH	
		SZE	DRAWING No.	REV
		С	PSC-4008	06
				*